

PATENT APPLICATION
IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of

Docket No: Q76117

KIYOKU, Hiroyuki, et al.

Divisional Application of Appln. No.: 10/261,487

Confirmation No.: Unknown

Prior Group Art Unit: 2822

Filed: June 23, 2003

Prior Examiner: Stephen D. Meier

For: NITRIDE SEMICONDUCTOR GROWTH METHOD, NITRIDE SEMICONDUCTOR
SUBSTRATE, AND NITRIDE SEMICONDUCTOR DEVICE

INFORMATION DISCLOSURE STATEMENT
UNDER 37 CFR §§ 1.97 and 1.98

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

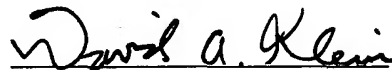
In accordance with the duty of disclosure under 37 CFR §1.56, Applicants hereby notify the U.S. Patent and Trademark Office of the documents which are listed on the attached Forms PTO-1449 and PTO/SB A & B (modified; four sheets), which are of record in parent Application No. 10/261,487. Applicants are not submitting duplicate copies of these references but request that they be listed on the face of any patent granted on the above application. (See 37 CFR §1.98(d)).

The submission of the listed documents is not intended as an admission that any such document constitutes prior art against the claims of the present application. Applicants do not

INFORMATION DISCLOSURE STATEMENT
Divisional Application No. 10/261,487

waive any right to take any action that would be appropriate to antedate or otherwise remove any listed document as a competent reference against the claims of the present application.

Respectfully submitted,



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WASHINGTON OFFICE



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PATENT TRADEMARK OFFICE

Date: June 23, 2003

Form PTO-1449 (Rev. 2-32)		U.S. Department of Commerce Patent & Trademark Office		Atty. Docket No. Q76117		Serial No.: Confirmation No.: To be Assigned	
INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)				Applicant: Hiroyuki KIYOKU, <i>et al.</i>			
				Filing Date: 06/23/03		Prior Art Group: 2822	
U.S. PATENT DOCUMENTS							
Examiner Initial		Document Number	Date	Name	Class	Sub-Class	Filing Date (if appropriate)
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EXAMINER:				DATE CONSIDERED:			
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